TOSHIBA Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

TPD1024S

Low-Side Power Switch for Motors, Solenoids, and Lamp Drivers

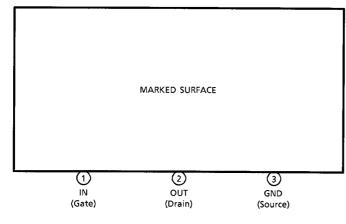
TPD1024S is a monolithic power IC for low-side switches. The IC has a vertical MOS FET output which can be directly driven from a CMOS or TTL logic circuit (e.g. an MPU).

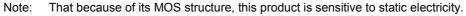
The device offers intelligent self-protection function

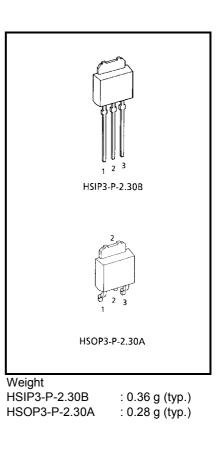
Features

- A monolithic power IC with a new structure combining a control block and a vertical power MOS FET (π -MOS) on a single chip.
- Can directly drive a power load from a CMOS logic.
- Built-in protection against overvoltage, load short circuiting, and thermal shutdown.
- Low on resistance : $R_{DS}(ON) = 0.5 \Omega(max)$, (@VIN = 5 V, T_j = 25°C)
- 3-pin power-molded package usable for surface mounting.

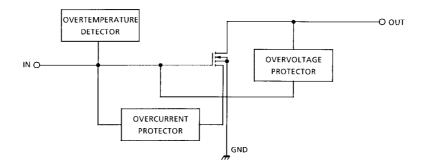
Pin Assignment







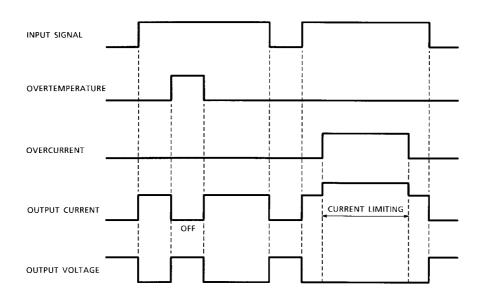
Block Diagram



Pin Description

Pin No.	Symbol	Function
1	IN	Input pin. Input is CMOS-compatible, with pull-down resistor connected. Even if the input is open, output will not accidentally turn on.
2	OUT	Output pin. When current in excess of the typical current (3.5 A (typ.)) flows to the output pin, the current limiter operates to protect the IC.
3	GND	Ground pin.

Timing Chart



Maximum Ratings (Ta = 25°C)

Characteri	stic	Symbol	Rating	Unit	
Drain-source voltage		V _{DS (DC)}	40	V	
Output current		I _D	1.5	А	
Input voltage		V _{GS}	-0.5 ~ 6	V	
Power dissipation	Ta = 25°C	PD	1	W	
rower dissipation	Tc = 25°C	гD	10	vv	
Operating temperature		T _{opr}	-40 ~ 85	°C	
Junction temperature		Тj	150	°C	
Storage temperature		T _{stg}	-55 ~ 150	°C	

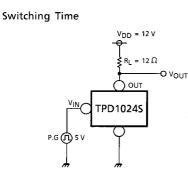
Recommendable Condition

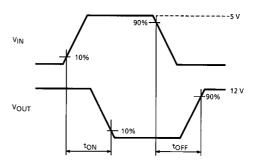
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Input voltage	V _{IN}	—	4.5	5	6	V

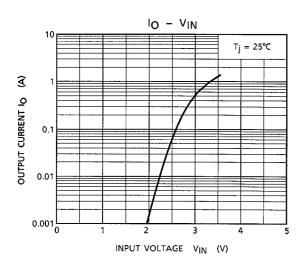
Electrical Characteristics ($T_j = 25^{\circ}C$)

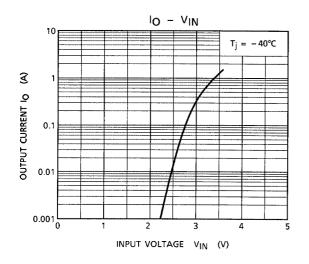
Characteristic	Symbol	Test Cir- cuit	Test Condition	Min	Тур.	Max	Unit
Drain-source breakdown voltage	V _(BR) DSS	_	V _{GS} = 0, I _D = 10 mA	40	—		V
Operating supply voltage	V _{DD (OPR)}	_	—	_	_	18	V
Current et output off	I _{DSS (1)}	_	V _{GS} = 0, V _{DS} = 40 V	_	_	3	mA
Current at output off	I _{DSS (2)}	_	V _{GS} = 0, V _{DS} = 24 V	_	_	100	μA
Input threshold voltage	V _{th}	—	V _{DS} = 10 V, I _D = 1 mA	0.8	_	2.5	V
Input current	IGSS	_	V _{GS} = 5 V, at normal operation	_	_	300	μA
On resistance	R _{DS (ON)}		V _{GS} = 5 V, I _D = 1 A	_	_	0.5	Ω
Thermal shutdown temperature	Τ _S		—	_	160	_	°C
Overcurrent protection	Is		V _{DS} = 12 V, V _{GS} = 5 V	_	3.5	_	А
Switching time	ton	- 1	V_{DS} = 12 V, V_{GS} = 5 V, R _L = 12 Ω		50	_	μs
Switching time	t _{OFF}				10		μs
Diode forward voltage Between drain and source	V _{DSF}	_	I _F = 1.5 A	_	0.9	1.8	V
Avalanche energy	E _A	—	L = 10 mH, Single pulse	30	—	_	mJ

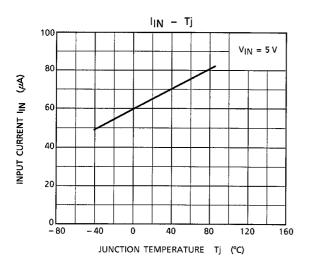
Test Circuit 1

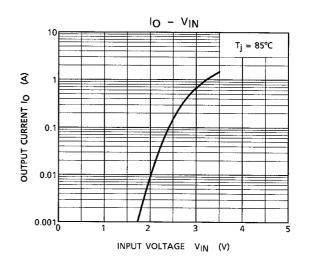


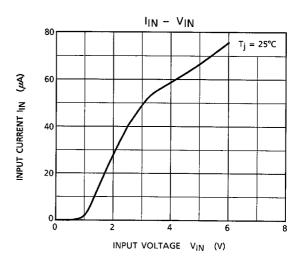


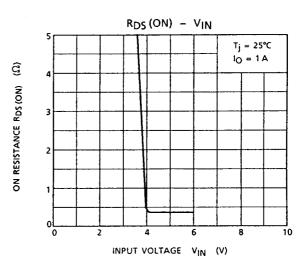












VIN = 5 V Tj = 25°C

10

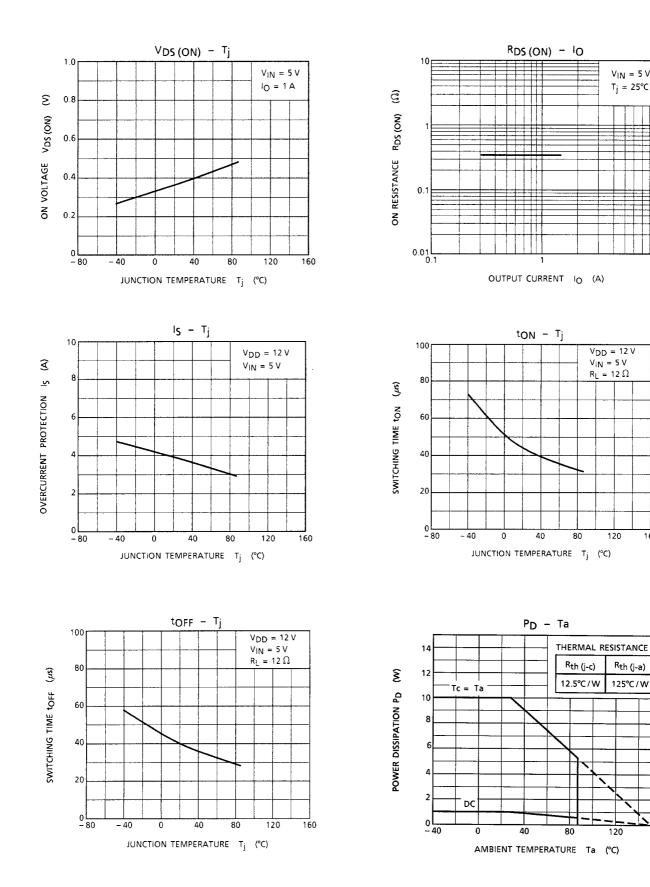
120

R_{th} (j-a)

125°C/W

120

160

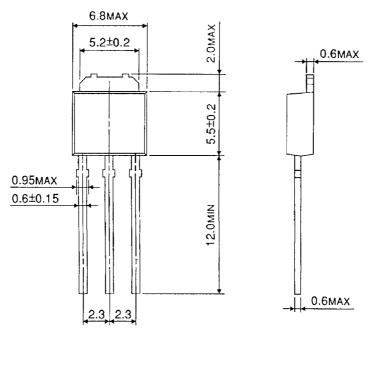


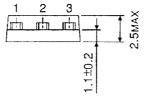
160

Package Dimenstions

HSIP3-P-2.30B

Unit : mm



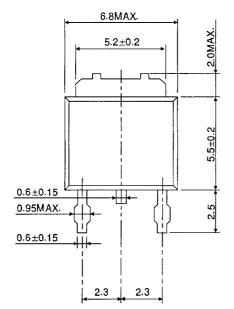


Weight: 0.36 g (typ.)

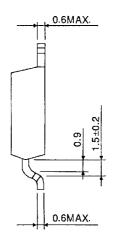
TPD1024S

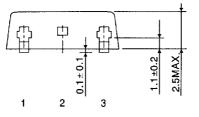
Package Dimenstions

HSOP3-P-2.30A



Unit : mm





Weight: 0.28 g (typ.)

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